Filing Date: October 8, 2003
Title: METHOD OF CLEANING SEMICONDUCTOR SURFACES

## IN THE SPECIFICATION

In the paragraph beginning on page 10, line 2, please make the following amendments.

Amended material was submitted in originally presented claims. No new matter is added.

Another advantage of methods and devices described above includes the ability to use supercritical fluid techniques with existing cleaning processes and cleaning solutions. For example, in a current dry cleaning process, de-ionized water is used to rinse a surface of a semiconductor surface. A supercritical fluid method as described above can be used to form bubbles in the de-ionized water. Likewise, in a wet cleaning example, a solution such as  $\rm H_2SO_4$  or  $\rm H_2O_2$  is used to clean the semiconductor surface. A supercritical fluid method as described above can be added to this wet cleaning example to form bubbles in the  $\rm H_2SO_4$  or  $\rm H_2O_2$  solutions. In one embodiment, a halogenated hydrocarbon carrier fluid is used. Examples of halogenated hydrocarbon carrier fluids include chlorocarbon fluids, and chlorofluorocarbon fluids. In processes such as those used for multichip assemblies where fluxes and or organic residues are present, chlorocarbons or chlorofluorocarbons may be used as a carrier fluid.